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Docket No.: M-12327 US

October 29, 2002

Commissioner For Patents  
Washington, D.C. 20231

Re: Applicant(s): Zhong Dong, Chuck Jang, Ching-Hwa Chen  
Assignee: Mosel Vitelic, Inc.  
Title: Floating Gate Nitridation  
Serial No.: 10/071,689  
Examiner: Pizarro Crespo, Marcos D.  
Docket No.: M-12327 US  
Filed: February 8, 2002  
Group Art Unit: 2814

Dear Sir:

Transmitted herewith are the following documents in the above-identified application:

- (1) Return Receipt Postcard;
- (2) This Transmittal Letter (in duplicate); and
- (3) Amendment (12 pages).

☒ The fee has been calculated as shown below:

**CLAIMS AS AMENDED**

	<u>Claims Remaining After Amendment</u>		<u>Highest No. Previously Paid For</u>		<u>Present Extra</u>		<u>Rate</u>		<u>Additional Fee</u>	
Total Claims	24	Minus	20	=	4	x	\$18.00	\$	72.00	
Independent Claims	3	Minus	4	=	0	x	\$84.00	\$	0.00	
<input type="checkbox"/>	Fee of _____ for the first filing of one or more multiple dependent claims per application							\$		
<input type="checkbox"/>	Fee for Request for Extension of Time							\$		
<b><u>Total additional fee for this Amendment:</u></b>								\$	<u>72.00</u>	
<input checked="" type="checkbox"/>	Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.									
<input checked="" type="checkbox"/>	Please charge our Deposit Account No. 19-2386 in the amount of							\$	<u>72.00</u>	
<input checked="" type="checkbox"/>	Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 19-2386.									
<b>Total:</b>								\$	<u>72.00</u>	

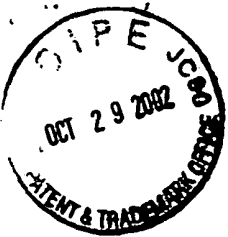
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Respectfully submitted,

*Michael Shenker*  
Michael Shenker  
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118-02  
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AMENDMENT

Dear Sir:

In reply to the Office Action dated August 14, 2002, please amend this application as follows (a version with markings to show changes made appears at the end):

11/01/2002 JADD01  
01 FC:1202

00000007 192306 10071689  
72.00 CH

IN THE SPECIFICATION

*Please amend the paragraph on page 3, lines 11-18, as follows:*

Fig. 2 illustrates a cross section of a nonvolatile memory cell at an early stage of fabrication. Semiconductor substrate 120 (monocrystalline silicon or some other material) is processed to form a suitably doped channel region 150 (type P in Fig. 2, but an N type channel can also be used). Dielectric 130 is formed on substrate 120 over channel 150. Dielectric 130 may be thermally grown silicon dioxide or some other type of dielectric. Then polysilicon layer 110 is deposited and doped during or after deposition. See for example U.S. patent application 09/640,139 filed August 15, 2000 and incorporated herein by reference (now U.S. patent no. 6,355,524 issued March 12, 2002).

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*Please amend the paragraph on page 5, lines 12-22, as follows:*

Known techniques can be used to complete the memory fabrication. In the example of Fig. 4, silicon nitride layer 410 is formed by low pressure CVD (LPCVD) on layer 310.